

M-plane GaN Substrates

Features	Units	Conductivity		
		n-type	p-type	SI
Carrier concentration	cm ⁻³	~ 10 ¹⁹	-	-
Resistivity	Ω·cm	10 ⁻³ - 10 ⁻²	-	-
Mobility	cm ² /V·s	~ 150	-	-
Thickness	μm	300-400	-	-
Total thickness variation (TTV)	μm	~ 20	-	-
Bow	μm	≤ 10	-	-
FWHM of X-ray rocking curve, (epi-ready surface at 100 μm x 100 μm slit)	arcsec	~ 30	-	-
Dislocation density	cm ⁻²	< 10 ⁵	-	-
Misorientation	deg	On demand		
Surface finishing		As cut / ground Roughly polished Optically polished (RMS < 3 nm) Epi-ready (RMS < 0.5 nm)		
Available sizes	mm	10x10, 13x15		
Packaging		Separate single wafer container		
Special Order Option		Please, contact Sales Department		

